

FORM PTO-117 DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		DOCKET 0019451 SVP03 ETCH SILICON JB			APPLICATION NO. 09/507,629		
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)		APPLICANT: SHEN et al			GROUP PART UNIT 1763		
		FILING DATE 02/18/2000					
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
fu	5,259,923	11/9/1993	HORI et al				
fu	5,384,009	1/24/1995	MAK et al				
fu	5,189,464	1/19/1993	TAJISUMI et al				
fu	6,270,634	8/2/2001	KUMAR et al				
fu	6,125,859	10/3/2000	KAO et al				
fu	5,861,233	1/19/1999	SEKINE et al				

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	ABSTRACT	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
fu	Kamizuka, Masakatsu et al "Pattern Profile Control in Magnetron reactive ion etching of Poly-Si." J. Vac. Sci. Technol. B 10(5), Sept/Oct 1992, pp. 2192-2196.						

EXAMINER: Allen Ober				DATE CONSIDERED: 5/24/03			
EXAMINER: initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							